Dual 4-Input NAND Gates

The MC14012B dual 4-input NAND gates are constructed with P-Channel and N-Channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low–Power TTL Loads or One Low–Power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to VSS)

| Symbol | Parameter | Value | Unit |
|------------------------------------|--|-------------------------------|------|
| V _{DD} | DC Supply Voltage Range | -0.5 to +18.0 | V |
| V _{in} , V _{out} | Input or Output Voltage Range (DC or Transient) | –0.5 to V _{DD} + 0.5 | V |
| I _{in} , I _{out} | Input or Output Current (DC or Transient) per Pin | ±10 | mA |
| PD | Power Dissipation, per Package (Note 1) | 500 | mW |
| T _A | Ambient Temperature Range | -55 to +125 | °C |
| T _{stg} | Storage Temperature Range | -65 to +150 | °C |
| ΤL | Lead Temperature (8–Second Soldering) | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Package: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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SOIC-14 D SUFFIX CASE 751A

MARKING DIAGRAM



A= Assembly LocationWL, L= Wafer LotYY, Y= YearWW, W= Work WeekG= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MC14012B **Dual 4–Input NAND Gate**

| $IN 4_A D 5$ 10 D IN 2 _B | $\begin{array}{c}3\\4\\5\\10\\11\\12\\12\\12\\12\\12\\12\\12\\12\\12\\12\\12\\12\\$ |
|--|---|
| NC $\begin{bmatrix} 6 & 9 \end{bmatrix}$ IN 1 _B | NC = 6, 8 |
| V _{SS} $\begin{bmatrix} 7 & 8 \end{bmatrix}$ NC | V_{DD} = PIN 14 |
| NC = NO CONNECTION | V_{SS} = PIN 7 |
| Figure 1. Pin Assignment | Figure 2. Logic Diagram |

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------|----------------------|--------------------------|
| MC14012BDG | SOIC-14 (Pb-Free) | 55 Units / Rail |
| NLV14012BDG* | SOIC-14 (Pb-Free) | 55 Units / Rail |
| MC14012BDR2G | SOIC-14 (Pb-Free) | 2500 Units / Tape & Reel |
| NLV14012BDR2G* | SOIC-14 (Pb-Free) | 2500 Units / Tape & Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 *NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.

| | | | | –55°C | | | 25°C | | 125°C | | |
|---|-----------|-----------------|------------------------|---|----------------------|-------------------------------|--------------------------------|----------------------|-------------------------------|----------------------|------|
| Characteristic | | Symbol | V _{DD} Vdc | Min | Max | Min | Typ (Note 2) | Мах | Min | Max | Unit |
| Output Voltage $V_{in} = V_{DD}$ or 0 | "0" Level | V _{OL} | 5.0 10 15 | - - - | 0.05 0.05 0.05 | - - - | 0 0 0 | 0.05 0.05 0.05 | - - - | 0.05 0.05 0.05 | Vdc |
| $V_{in} = 0 \text{ or } V_{DD}$ | "1" Level | V _{OH} | 5.0 10 15 | 4.95 9.95 14.95 | - - - | 4.95 9.95 14.95 | 5.0 10 15 | - - - | 4.95 9.95 14.95 | - - - | Vdc |
| Input Voltage $(V_O = 4.5 \text{ or } 0.5 \text{ Vdc})$ $(V_O = 9.0 \text{ or } 1.0 \text{ Vdc})$ $(V_O = 13.5 \text{ or } 1.5 \text{ Vdc})$ | "0" Level | VIL | 5.0 10 15 | _ _ _ | 1.5 3.0 4.0 | _ _ _ | 2.25 4.50 6.75 | 1.5 3.0 4.0 | _ _ _ | 1.5 3.0 4.0 | Vdc |
| $(V_{O} = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_{O} = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_{O} = 1.5 \text{ or } 13.5 \text{ Vdc})$ | "1" Level | V _{IH} | 5.0 10 15 | 3.5 7.0 11 | _ _ _ | 3.5 7.0 11 | 2.75 5.50 8.25 | | 3.5 7.0 11 | _ _ _ | Vdc |
| $\begin{array}{l} \text{Output Drive Current} \\ (\text{V}_{\text{OH}} = 2.5 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 4.6 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 9.5 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 13.5 \ \text{Vdc}) \end{array}$ | Source | I _{OH} | 5.0 5.0 10 15 | -3.0 -0.64 -1.6 -4.2 | - - - | -2.4 -0.51 -1.3 -3.4 | -4.2 -0.88 -2.25 -8.8 | - - - | -1.7 -0.36 -0.9 -2.4 | - - - | mAdo |
| (V _{OL} = 0.4 Vdc) (V _{OL} = 0.5 Vdc) (V _{OL} = 1.5 Vdc) | Sink | I _{OL} | 5.0 10 15 | 0.64 1.6 4.2 | - - - | 0.51 1.3 3.4 | 0.88 2.25 8.8 | | 0.36 0.9 2.4 | - - - | mAdo |
| Input Current | | l _{in} | 15 | _ | ±0.1 | - | ±0.00001 | ±0.1 | _ | ±1.0 | μAdc |
| Input Capacitance (V _{in} = 0) | | C _{in} | _ | - | - | - | 5.0 | 7.5 | - | _ | pF |
| Quiescent Current (Per Package) | | I _{DD} | 5.0 10 15 | - - - | 0.25 0.5 1.0 | - - - | 0.0005 0.0010 0.0015 | 0.25 0.5 1.0 | - - - | 7.5 15 30 | μAdc |
| Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Gate, C _L = 50 pF) | | Ι _Τ | 5.0 10 15 | $\begin{split} I_{T} &= (0.3 \; \mu \text{A/kHz}) \; \text{f} + I_{\text{DD}}/\text{N} \\ I_{T} &= (0.6 \; \mu \text{A/kHz}) \; \text{f} + I_{\text{DD}}/\text{N} \\ I_{T} &= (0.9 \; \mu \text{A/kHz}) \; \text{f} + I_{\text{DD}}/\text{N} \end{split}$ | | | | | - | μAdc | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

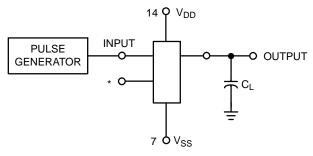
 $I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$

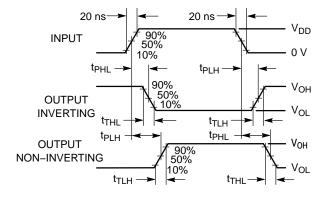
where: I_T is in μA (per package), C_L in pF, V = ($V_{DD} - V_{SS}$) in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

SWITCHING CHARACTERISTICS (Note 5) (CL = 50 pF, TA = 25° C)

| Characteristic | Symbol | V _{DD} Vdc | Min | Typ (Note 6) | Max | Unit |
|--|-------------------------------------|------------------------|-------------|-----------------|-------------------|------|
| Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) \text{ C}_L + 33 \text{ ns}$ $t_{TLH} = (0.60 \text{ ns/pF}) \text{ C}_L + 20 \text{ ns}$ $t_{TLH} = (0.40 \text{ ns/PF}) \text{ C}_L + 20 \text{ ns}$ | t _{TLH} | 5.0 10 15 | - - - | 100 50 40 | 200 100 80 | ns |
| Output Fall Time t _{THL} = (1.35 ns/pF) C _L + 33 ns t _{THL} = (0.60 ns/pF) C _L + 20 ns t _{THL} = (0.40 ns/pF) C _L + 20 ns | t _{THL} | 5.0 10 15 | _ _ _ | 100 50 40 | 200 100 80 | ns |
| Propagation Delay Time $t_{PLH}, t_{PHL} = (0.90 \text{ ns/pF}) \text{ C}_{L} + 115 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.36 \text{ ns/pF}) \text{ C}_{L} + 47 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.26 \text{ ns/pF}) \text{ C}_{L} + 37 \text{ ns}$ | t _{PLH} , t _{PHL} | 5.0 10 15 | - - - | 160 65 50 | 300 130 100 | ns |

The formulas given are for the typical characteristics only at 25°C.
 Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.





*All unused inputs of AND, NAND gates must be connected to $V_{\text{DD}}.$ All unused inputs of OR, NOR gates must be connected to $V_{\text{SS}}.$

Figure 3. Switching Time Test Circuit and Waveforms

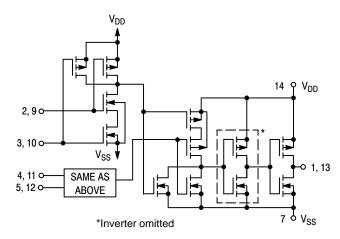


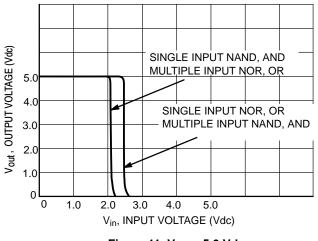
Figure 4. Circuit Schematic – One of Two Gates Shown

N-CHANNEL DRAIN CURRENT (SINK) P-CHANNEL DRAIN CURRENT (SOURCE) -10 5.0 -9.0 -8.0 4.0 $T_A = -55^{\circ}C$ ID, DRAIN CURRENT (mA) ID, DRAIN CURRENT (mA) -7.0 $T_A = -55^{\circ}C$ -40°C 3.0 -6.0 40°C -5.0 +25°C +25°C +85°C +85°C 2.0 -4.0 +125°C -3.0 +125°C -2.0 1.0 -1.0 0 0 1.0 2.0 3.0 4.0 5.0 -2.0 -3.0 -4.0 -5.0 0 -1.0 0 V_{DS}, DRAIN-TO-SOURCE VOLTAGE (Vdc) V_{DS}, DRAIN-TO-SOURCE VOLTAGE (Vdc) Figure 6. V_{GS} = - 5.0 Vdc Figure 5. V_{GS} = 5.0 Vdc 20 -50 -45 18 $T_A = -55^{\circ}C$ -40 16 ID, DRAIN CURRENT (mA) ID, DRAIN CURRENT (mA) 14 -40°C -35 -55°Ċ +25°C 12 $T_A = \cdot$ -30 +<u>85°C</u> 10 -25 -40°C + 25°C +125°C 8.0 -20 +85°C 6.0 -15 +125°C 4.0 -10 2.0 -5.0 0 0 2.0 3.0 4.0 5.0 6.0 7.0 8.0 -1.0 -2.0 -3.0 -4.0 -5.0 -6.0 -7.0 -8.0 -9.0 -10 1.0 9.0 10 0 0 V_{DS}, DRAIN-TO-SOURCE VOLTAGE (Vdc) V_{DS}, DRAIN-TO-SOURCE VOLTAGE (Vdc) Figure 7. V_{GS} = 10 Vdc Figure 8. V_{GS} = - 10 Vdc 50 - 100 45 - 90 40 - 80 ID, DRAIN CURRENT (mA) ID, DRAIN CURRENT (mA) 35 $T_A = -55^{\circ}C$ - 70 30 - 60 -40°C $T_A = -55^{\circ}C$ 25 - 50 +25°C 40°C +85°C +25°C 20 - 40 +85°C +125°C 15 - 30 +125°C 10 - 20 5.0 - 10 0 0 0 4.0 8.0 10 12 14 16 18 -2.0 -4.0 -6.0 -8.0 -10 -12 -14 -16 -18 -20 2.0 6.0 20 0 V_{DS}, DRAIN-TO-SOURCE VOLTAGE (Vdc) V_{DS}, DRAIN-TO-SOURCE VOLTAGE (Vdc) Figure 9. V_{GS} = 15 Vdc Figure 10. $V_{GS} = -15$ Vdc

TYPICAL B-SERIES GATE CHARACTERISTICS

These typical curves are not guarantees, but are design aids. Caution: The maximum rating for output current is 10 mA per pin.

VOLTAGE TRANSFER CHARACTERISTICS





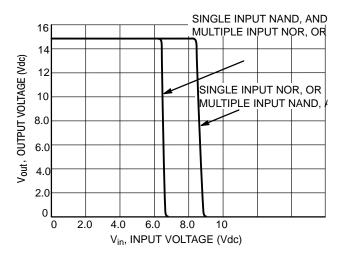
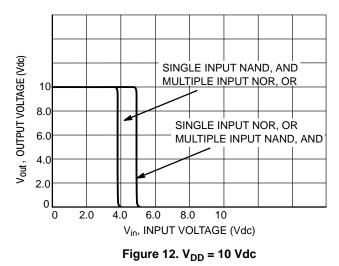


Figure 13. V_{DD} = 15 Vdc



DC NOISE MARGIN

The DC noise margin is defined as the input voltage range from an ideal "1" or "0" input level which does not produce output state change(s). The typical and guaranteed limit values of the input values V_{IL} and V_{IH} for the output(s) to be at a fixed voltage V_O are given in the Electrical Characteristics table. V_{IL} and V_{IH} are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the "1" and "0" levels =

1.0 V with a 5.0 V supply 2.0 V with a 10.0 V supply 2.5 V with a 15.0 V supply

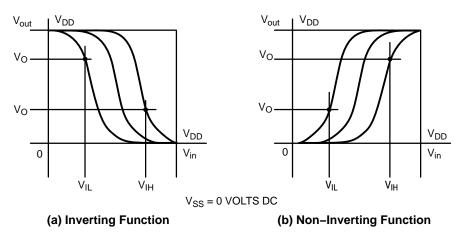
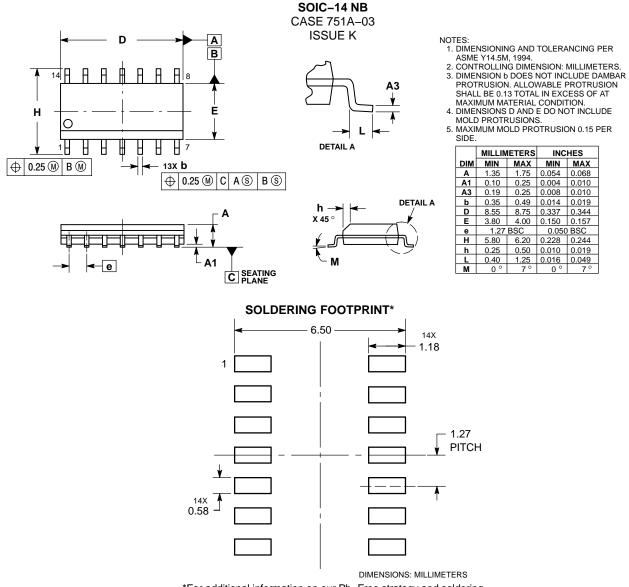


Figure 14. DC Noise Immunity

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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